

Title (en)

Static induction thyristor and method of fabricating same.

Title (de)

Statischer Induktionsthyristor und dessen Herstellungsverfahren.

Title (fr)

Thyristor à induction statique et son procédé de fabrication.

Publication

EP 0680093 A2 19951102 (EN)

Application

EP 95302909 A 19950428

Priority

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Abstract (en)

A P<+> layer 12 is formed on the lower surface of an N<-> substrate 10, and recesses 40 are defined in the upper surface of the N<-> substrate 10. Then, P<+> gate regions 32 and bottom gate regions 34 are formed in side walls 42 and bottoms 44 of the recesses 40. The N<-> substrate 10 and an N<-> substrate 20 are ultrasonically cleaned to remove impurities therefrom, then cleaned by pure water, and dried by a spinner. Then, while lands 14 on the upper surface of the N<-> substrate 10 are being held against the surface of the N<-> substrate 20, the N<-> substrates 10, 20 are joined to each other by heating them at 800 DEG C in a hydrogen atmosphere. <IMAGE>

IPC 1-7

H01L 29/739; **H01L 21/332**

IPC 8 full level

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CPC (source: EP US)

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